

IGBT Transistor Module

MG8Q6ES42

1200V / 8A

DATASHEET

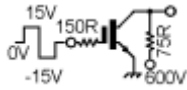
OEM – Toshiba

Source: Toshiba Databook 1995/96

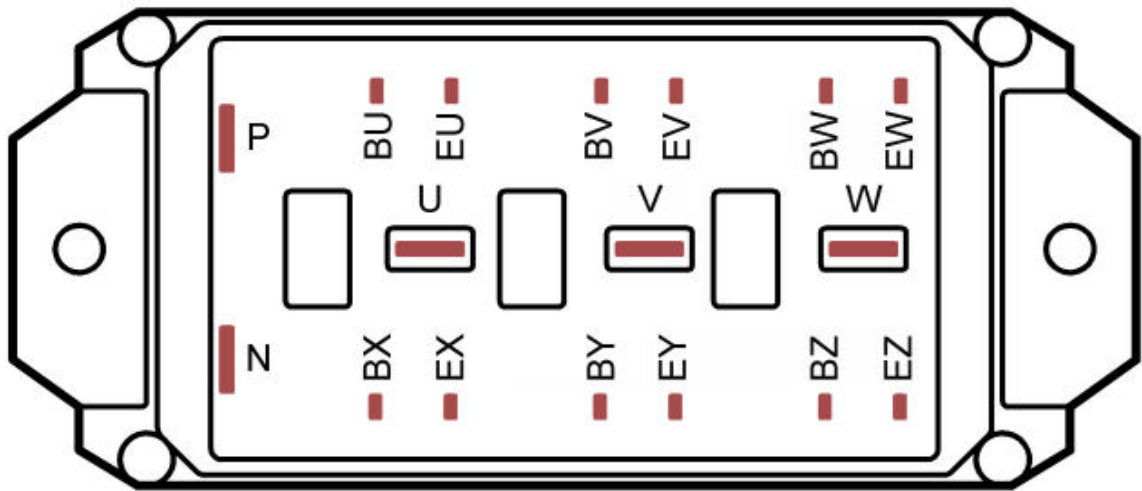
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	Vces	1200	V
Gate-Emitter Voltage	Vges	+/-20	V
Collector Current	DC	IC	8
	1ms	Icp	16
Forward Current	DC	If	8
	1ms	Ifm	16
Collector Power Dissipation	Pc	80	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-40~125	°C
Isolation Voltage	Visol	2500 (AC 1min.)	V
Screw Torque	-	3	N*m

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	Iges	Uge=+/-20V, Vce=0	-	-	+10	uA
Collector Cut-off Current	Ices	Uce=1200V, Uge=0	-	-	1.0	mA
Gate-Emitter Cut-off Voltage	Uge (off)	Ic=8mA, Uce=5V	3.0	-	6.0	V
Collector-Emitter Saturation Voltage	Uce (sat)	IC=8A, Uge=15V	-	3.0	4.0	V
Input Capacitance	Cies	Uce=10V, Uge=0, f=1MHz	-	900	-	pF
Switching Time	Rise Time		-	0.30	0.60	uS
	Turn-on Time		-	0.40	0.80	
	Fall Time		-	0.25	0.50	
	Turn-off Time		-	0.8	1.50	
Forward Voltage	Vf	If=8A, Uge=0	-	1.4	2.5	V
Reverse Recovery Time	trr	If=8A, Uge=-10V di/dt=100A/uS	-	0.2	0.50	uS
Thermal Resistance	Rth (j-c)	Transistor	-	-	1.56	°C/W
		Diode	-	-	1.8	

2-93A3A



EQUIVALENT CIRCUIT

